

Title (en)
DIE ATTACHMENT EXHIBITING ENHANCED QUALITY AND RELIABILITY.

Title (de)
HALBLEITERWÜRFEL-VERBINDUNG MIT VERBESSERTER QUALITÄT UND ZUVERLÄSSIGKEIT.

Title (fr)
FIXATION D'UN DE DE QUALITE ET FIABILITE AMELIOREES.

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Application
EP 81901580 A 19801230

Priority
US 8001746 W 19801230

Abstract (en)
[origin: WO8202457A1] A method of attaching a silicon IC chip (10) to a metal or ceramic substrate (38) includes coating the underside of the die with a barrier material (32), such as chromium, and then coating the first layer with another material (34) selected from the group consisting of silver, gold, tin, antimony, or alloys thereof. A preform (36) of material selected from the group consisting of tin, tin with a relatively small amount of antimony, or tin with a relatively small amount of antimony and a trace of aluminum is then placed on the heated substrate (38) followed by the die (10) to effect attachment.

Abstract (fr)
Un procede de fixation d'une pastille IC (de circuit integre) de silicium (10) sur un substrat metallique de ceramique (38) consiste a revetir le dessous du de d'un materiau-barriere (32), tel que du chrome, puis a revetir la premiere couche d'un autre materiau (34) selectionne parmi le groupe constitue par l'argent, l'or, l'etain, l'antimoine, ou leurs alliages. Une preforme (36) de materiau selectionne parmi le groupe constitue par l'etain, l'etain avec une quantite relativement petite d'antimoine, ou l'etain avec une quantite relativement petite d'antimoine et de l'aluminium a l'etat de traces et ensuite placee sur le substrat chauffe (38) suivi du de (10) pour effectuer la fixation.

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